

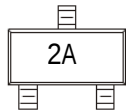
SOT-23 Plastic-Encapsulate Transistors

MMBT3906

MMBT3906 TRANSISTOR (PNP)

FEATURES

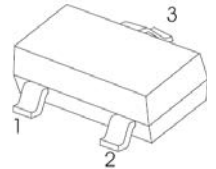
- As complementary type, the NPN transistor MMBT3904 is Recommended
- Epitaxial planar die construction



2A= Device code

Solid dot = Green molding compound device, if none, the normal device.

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1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
P_C	Collector Dissipation	0.2	W
$R_{\theta JA}$	Thermal resistance junction to ambient	625	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40\text{V}, I_E=0$		-100	nA
Collector cut-off current	I_{CEX}	$V_{CE}=-30\text{V}, V_{BE(off)}=-3\text{V}$		-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$		-100	nA
DC current gain	h_{FE1}	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	100	300	
	h_{FE2}	$V_{CE}=-1\text{V}, I_C=-50\text{mA}$	60		
	h_{FE3}	$V_{CE}=-2\text{V}, I_C=-100\text{mA}$	30		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50\text{mA}, I_B=-5\text{mA}$		-0.95	V
Transition frequency	f_T	$V_{CE}=-20\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	300		MHz
Delay Time	t_d	$V_{CC}=-3\text{V}, V_{BE}=-0.5\text{V}$ $I_C=-10\text{mA}, I_{B1}=I_{B2}=-1\text{mA}$		35	nS
Rise Time	t_r			35	nS
Storage Time	t_s			225	nS
Fall Time	t_f	$I_{B1}=I_{B2}=-1\text{mA}$		75	nS

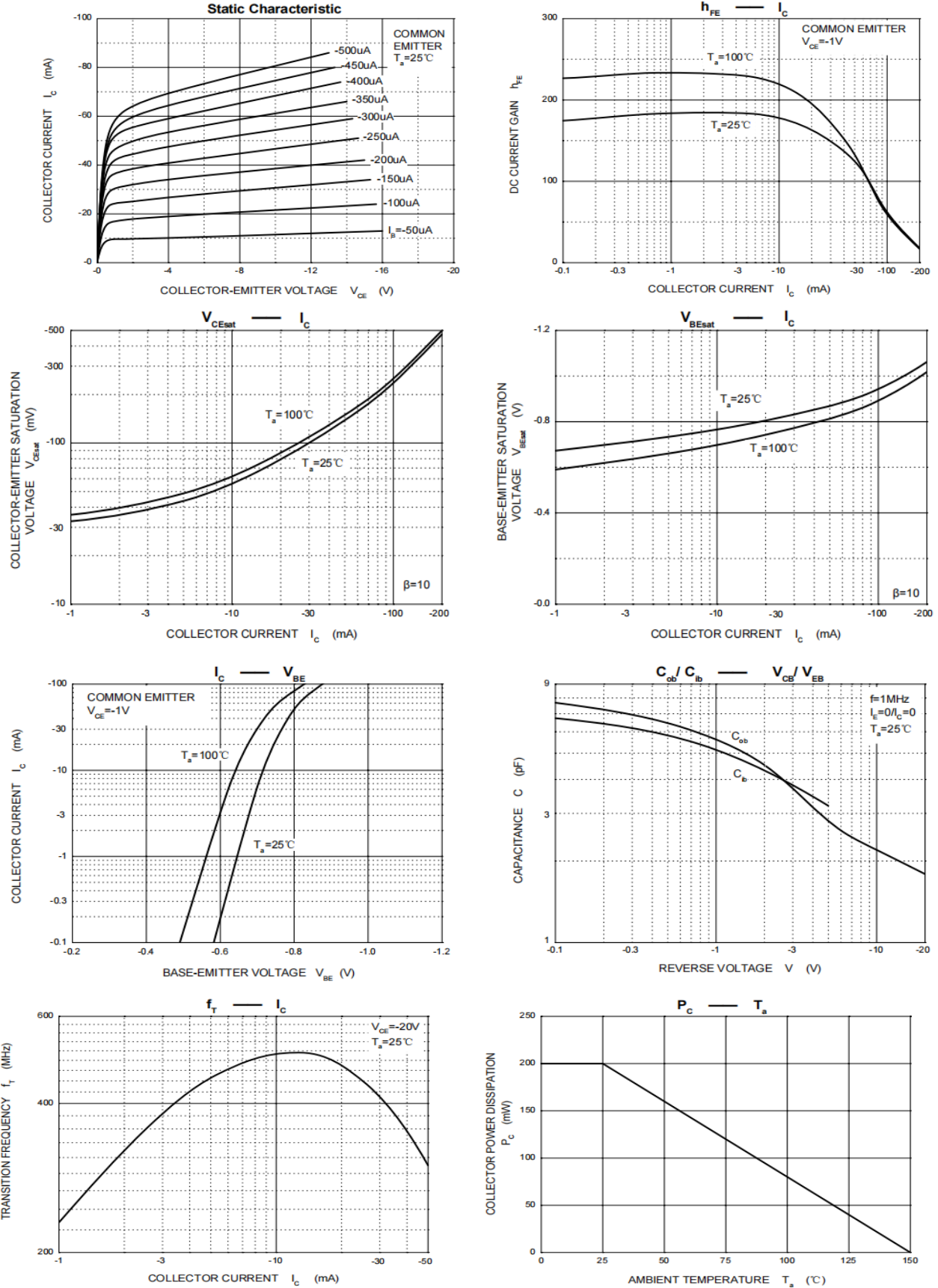
CLASSIFICATION OF $h_{FE(1)}$

HFE	100-300	
RANK	L	H
RANGE	100 - 200	200 - 300

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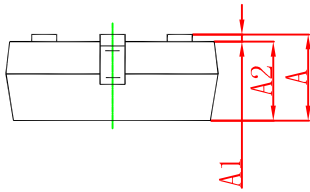
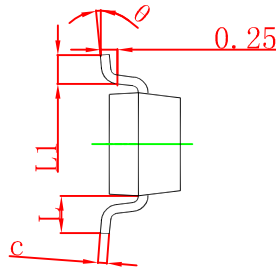
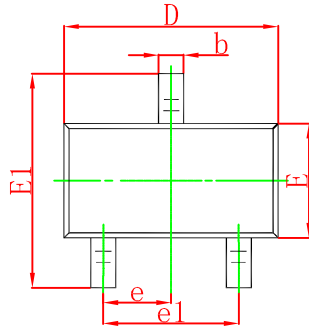
Typical Characteristics



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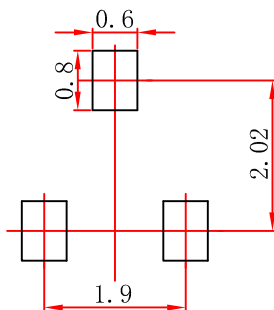
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SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.